

## Material Technology by New Plasma- and Ion Beam Techniques

# Heaters for Ion Beam- and Plasma Processing

## 1 Application

Heaters for ion beam- and plasma processing operate at the temperature range up to 500 C. Mostly they are halogen lamp based and used for:

- Substrate heater for ion beam- and plasma processing generated from plasma- and ion sources operating at high vacuum,
- Substrate heater for plasma processing with plasma reactors or plasma sources operating in the mbar- range,

- Heaters for heating of high temperature ion beam- and plasma sources.

Together with our Plasma- and Ion Sources [1,2,4,5] and inline substrate holders [4] cost effective systems for ion beam and plasma processing in existing or new vacuum equipment can be installed used for research and development and small scale industrial production.

## 2 Overview heaters

Tab.1 gives an overview about the heaters.

	Substrate heater for plasma processing	Substrate heater for ion beam processing	Ion beam- and plasma source heater
Heater elements	halogen lamps	halogen lamps	halogen lamps
Pressure range	$10^{-8}$ to 1000 mbar	$< 10^{-2}$ mbar	$< 10^{-2}$ mbar
Voltage	24 V	220 V	220 V
Heater power	0.1 to 3 kW	0.1 to 3 kW	0.1 to 3 kW
Thermoelement	type K	type K	type K
Control interface	analogue interface	analogue interface	analogue interface

Tab.1: Overview substrate heaters

The heaters consists of the halogen heater with dimensions dependent on the substrates and on the process equipment and of a electrical power unit with max. 3 kW heater power. The heaters used at high vacuum use halogen lamps for 220 V, the plasma process heater

use 24 V halogen lamps to avoid plasma break downs and arcing. By using conventional halogen lamps cost effective solutions can be build.

### 3 Application Examples

Two application examples are shown:

- a) **Heaters for heating of ion- or plasma sources for temperatures up to 400 C for generating of plasmas or ion beams of liqueous precursors or low melting point metals or isolators (fig.1).**
- b) **Substrate heaters in linear substrate transport mechanisms together with linear plasma or ion sources (fig.2).**

Like shown at fig.1 circular or linear ion- or plasma sources can be heated up to 400 C by a surrounding set of halogen lamps. The temperature is measured inside the source near the discharge plasma.

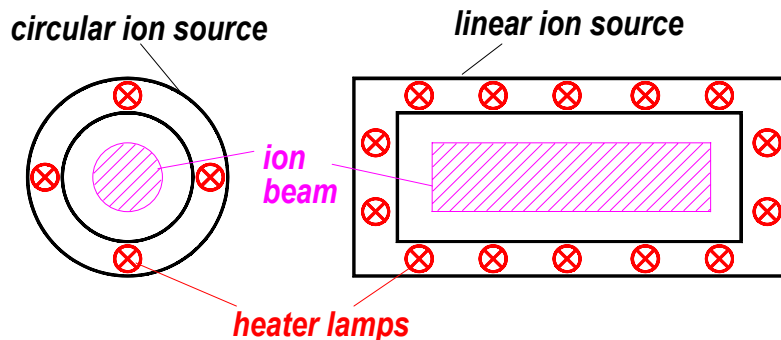


Fig.1: Principle of ion source heaters

Fig.2 shows the principle of heating substrates at a linear inline substrate holder used for ion beam or plasma processing with linear sources. The substrates moved by a linear

transport mechanism first come to the heater and are heated to the process temperature before the enter the process zone of the plasma- or ion source.

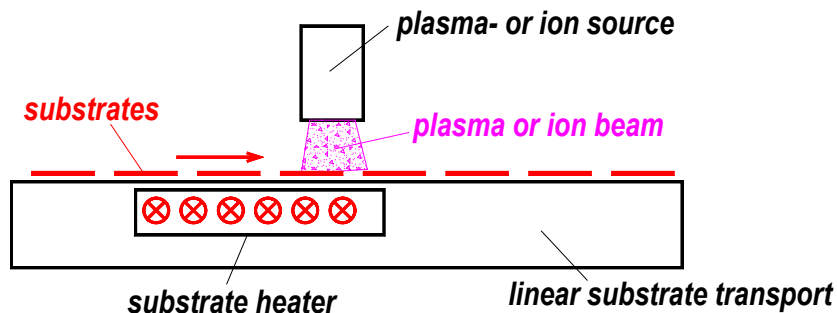


Fig.2: Principle of substrate heaters

### 4 References

- [1] "Alternating Cold Cathode Ion source JENION ACC-40 IS", product information , JENION 2003.
- [2] "Broad Beam Ion Implantation with linear ACC ion sources JENION ACC-30x150 IMP, ACC-40 x300 IMP and ACC-40x600 IMP " product information, JENION 2003.
- [3] "Linear substrate holders for plasma- and ion beam processing", product information JENION 2003.
- [4] "Linear ACC-ion sources ACC-30x150 IS, ACC-40 x 300 IS and ACC-40 x 600 IS", product information , JENION 2003.
- [5] "Alternating Cold Cathode Plasma Sources ", product information, JENION 2003.